

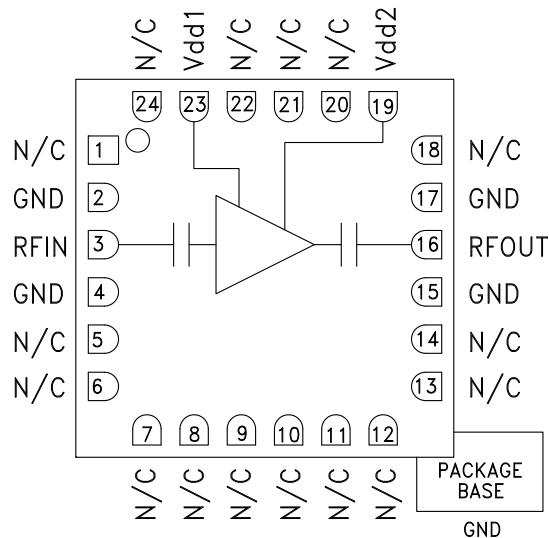
**GaAs SMT pHEMT LOW NOISE
AMPLIFIER, 7 - 14 GHz**

Typical Applications

The HMC564LC4 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military & Space

Functional Diagram



Features

- Noise Figure: 1.8 dB
- Gain: 17 dB
- OIP3: 25 dBm
- Single Supply: +3V @ 51 mA
- 50 Ohm Matched Input/Output
- RoHS Compliant 4 x 4 mm Package

General Description

The HMC564LC4 is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier housed in a leadless RoHS compliant 4x4 mm SMT package. Operating from 7 to 14 GHz, the HMC564LC4 features extremely flat small signal gain of 17 dB as well as 1.8 dB noise figure and +25 dBm output IP3 across the operating band. This self-biased LNA is ideal for microwave radios due to its consistent output power, single +3V supply operation, and DC blocked RF I/O's.

Electrical Specifications, $T_A = +25^\circ C$, $Vdd 1, 2 = +3V$

Parameter	Min.	Typ.	Max.	Units
Frequency Range		7 - 14		GHz
Gain	14	17		dB
Gain Variation Over Temperature		0.02	0.03	dB/ °C
Noise Figure		1.8	2.2	dB
Input Return Loss		15		dB
Output Return Loss		14		dB
Output Power for 1 dB Compression (P1dB)	10	13		dBm
Saturated Output Power (Psat)		14.5		dBm
Output Third Order Intercept (IP3)		25		dBm
Supply Current (Idd)(Vdd = +3V)		51	75	mA

HMC564LC4* PRODUCT PAGE QUICK LINKS

Last Content Update: 08/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

- HMC564LC4 Evaluation Board.

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

- HMC564LC4: GaAs SMT pHEMT Low Noise Amplifier, 7 - 14 GHz

TOOLS AND SIMULATIONS

- HMC564LC4 S-Parameters

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: LC4, LC4B (QTR: 2014-00380 REV: 01)
- Semiconductor Qualification Test Report: pHEMT-A (QTR: 2013-00267)

DESIGN RESOURCES

- HMC564LC4 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC564LC4 EngineerZone Discussions.

SAMPLE AND BUY

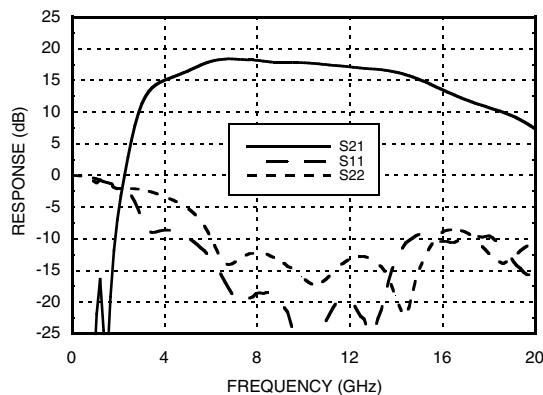
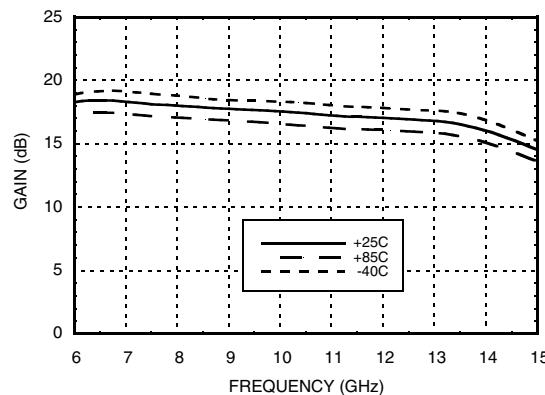
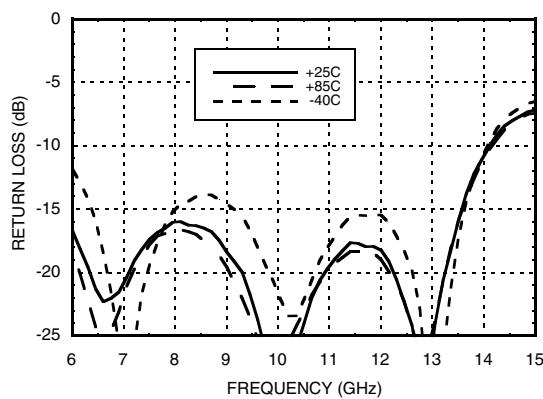
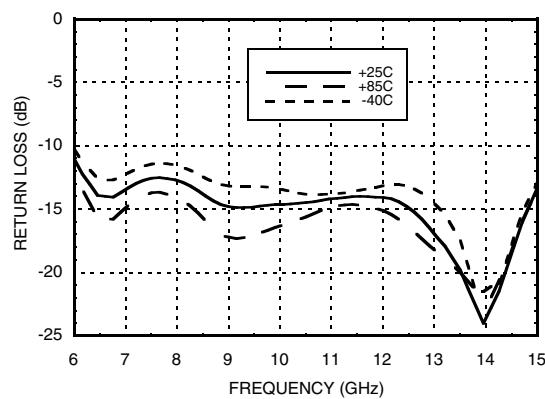
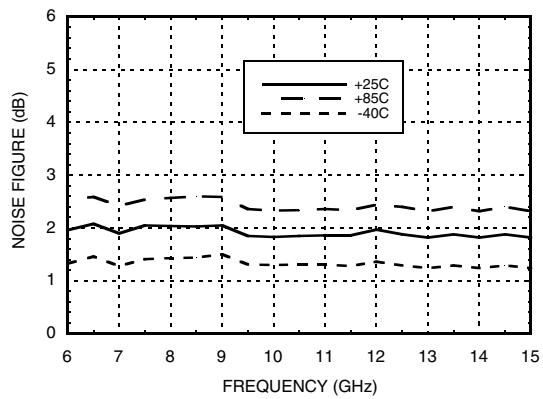
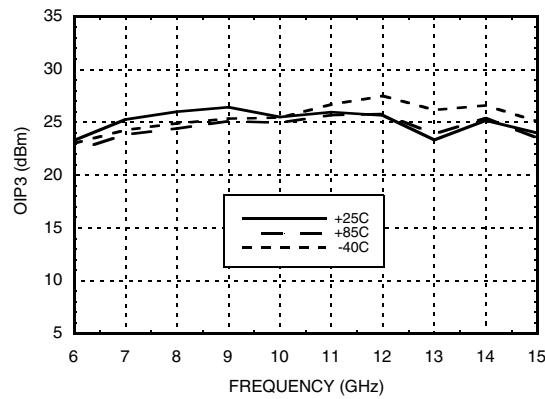
Visit the product page to see pricing options.

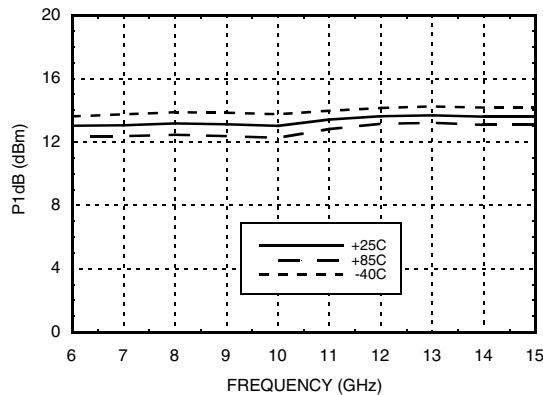
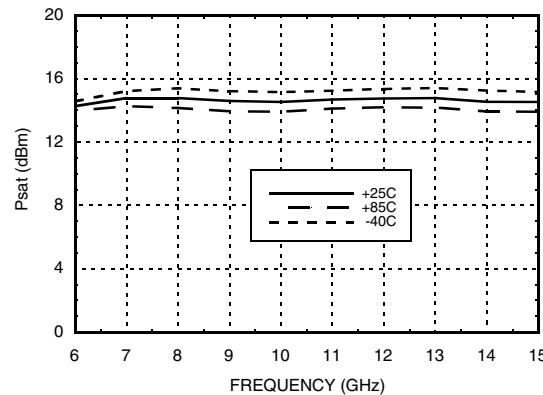
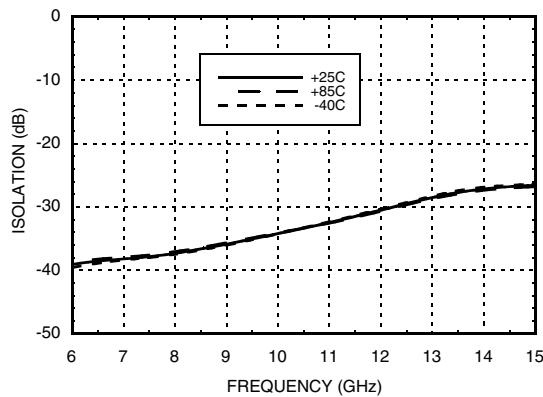
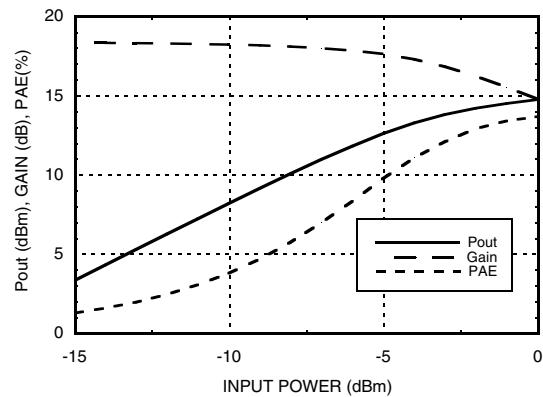
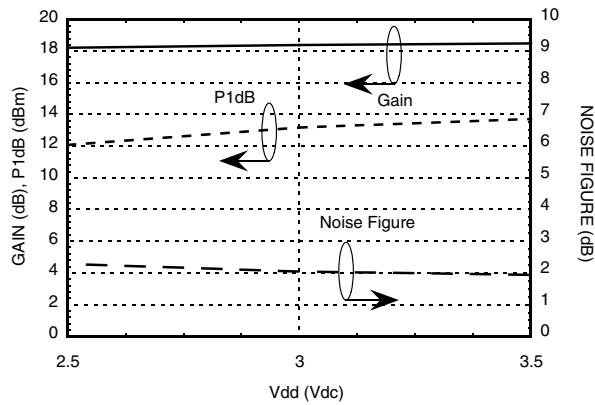
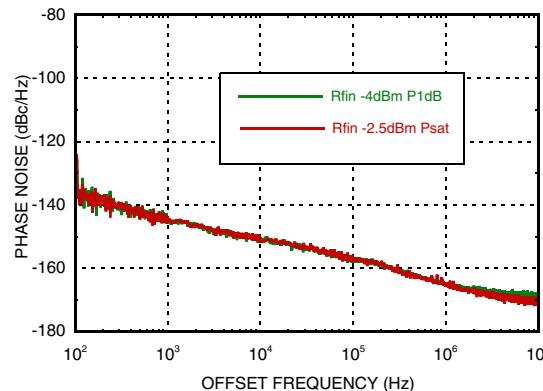
TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

Submit feedback for this data sheet.

**GaAs SMT pHEMT LOW NOISE
AMPLIFIER, 7 - 14 GHz**
Broadband Gain & Return Loss

Gain vs. Temperature

Input Return Loss vs. Temperature

Output Return Loss vs. Temperature

Noise Figure vs. Temperature

Output IP3 vs. Temperature


**GaAs SMT pHEMT LOW NOISE
AMPLIFIER, 7 - 14 GHz**
P1dB vs. Temperature

Psat vs. Temperature

Reverse Isolation vs. Temperature

Power Compression @ 8 GHz

**Gain, Power & Noise Figure
vs. Supply Voltage @ 8 GHz**

**Phase Noise vs. Offset Frequency
@11 GHz**


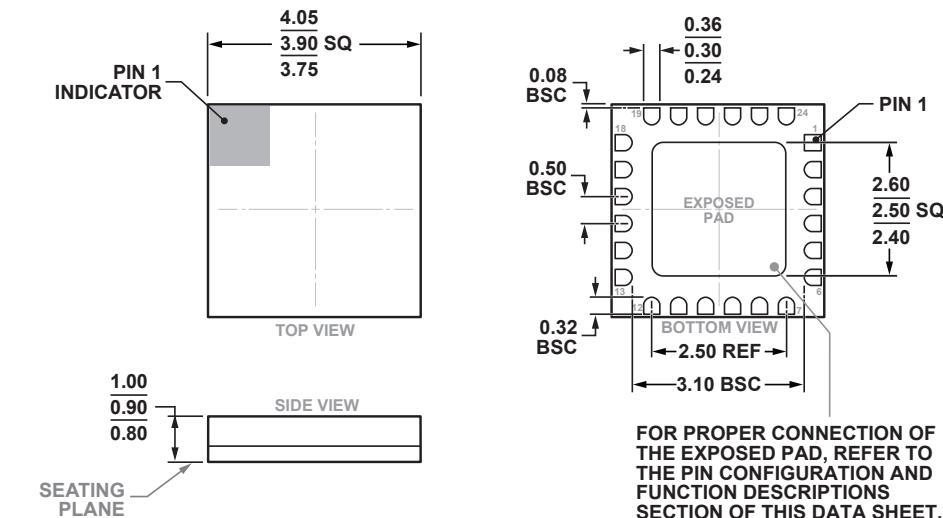
**GaAs SMT pHEMT LOW NOISE
AMPLIFIER, 7 - 14 GHz**
Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2)	+3.5 Vdc
RF Input Power (RFIN) (Vdd = +3.0 Vdc)	+5 dBm
Channel Temperature	175 °C
Continuous Pdiss (T = 85 °C) (derate 12.9 mW/°C above 85 °C)	1.16 W
Thermal Resistance (channel to ground paddle)	77.5 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
2.5	49
3.0	51
3.5	53

Note: Amplifier will operate over full voltage ranges shown above.


**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**
Outline Drawing

PKG-0048-00
02-27-2017-B

24-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-24-1)

Dimensions shown in millimeters.

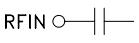
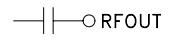
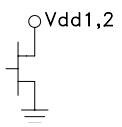
Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC564LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H564 XXXX
HMC564LC4TR	Alumina, White	Gold over Nickel	MSL3 ^[1]	H564 XXXX
HMC564LC4TR-R5	Alumina, White	Gold over Nickel	MSL3 ^[1]	H564 XXXX

[1] Max peak reflow temperature of 260 °C

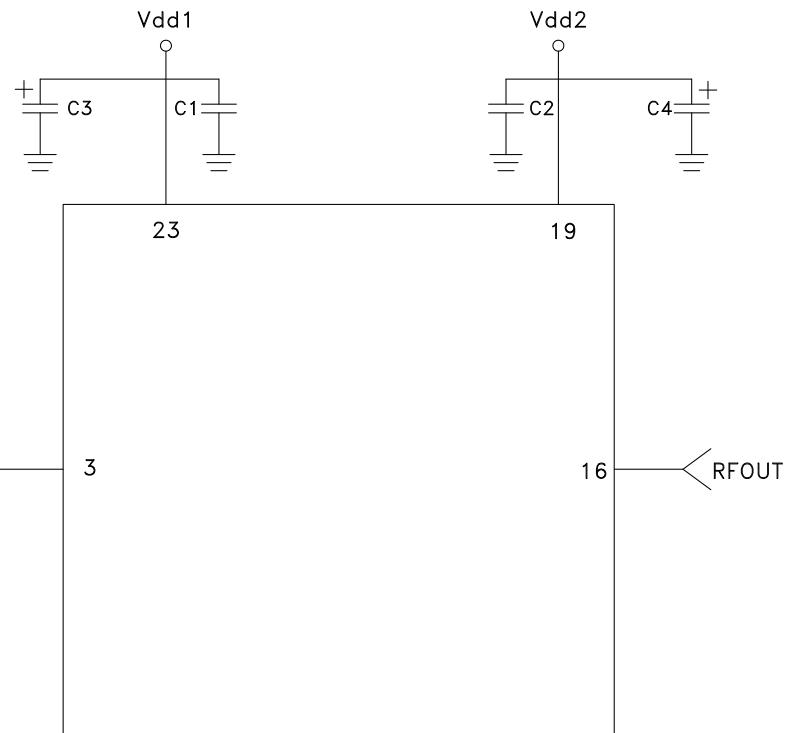
[2] 4-Digit lot number XXXX

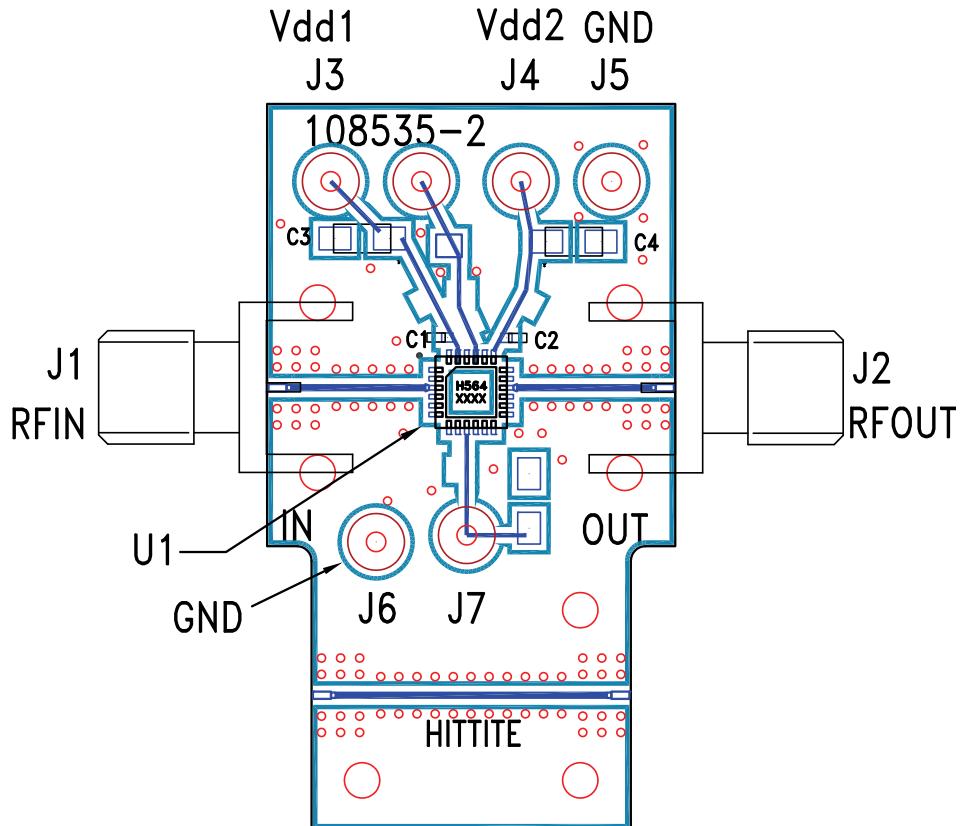
**GaAs SMT pHEMT LOW NOISE
AMPLIFIER, 7 - 14 GHz**
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5 -14, 18, 20, 21, 22, 24	N/C	No connection required. These pins may be connected to RF/DC ground without affecting performance.	
2, 4, 15, 17	GND	These pins and package bottom must be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
19, 23	Vdd1, Vdd2	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, and 2.2 μ F are required.	

Application Circuit

Component	Value
C1, C2	100 pF
C3, C4	2.2 μ F



Evaluation PCB**List of Material for Evaluation PCB 116156-HMC564LC4 [1]**

Item	Description
J1, J2	2.92 mm PC mount SMA
J3 - J7	DC Pin
C1 - C2	100 pF capacitor, 0402 Pkg..
C3 - C4	2.2 μ F Capacitor, Tantalum
U1	HMC564LC4 Amplifier
PCB [2]	108535 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350.

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.